

AA028P3-00

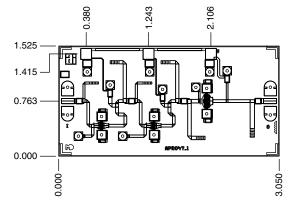
Features

- Single Bias Supply Operation (6 V)
- 19 dB Typical Small Signal Gain
- 16 dBm Typical P_{1 dB} Output Power at 28 GHz
- 0.25 µm Ti/Pd/Au Gates
- 100% On-Wafer RF and DC Testing
- 100% Visual Inspection to MIL-STD-883 MT 2010

Description

Alpha's three-stage reactively-matched 27–31 GHz GaAs MMIC driver amplifier has typical small signal gain of 19 dB with a typical P_{1 dB} of 16 dBm at 28 GHz. The chip uses Alpha's proven 0.25 μ m MESFET technology, and is based upon MBE layers and electron beam lithography for the highest uniformity and repeatability. The FETs employ surface passivation to ensure a rugged, reliable part with through-substrate via holes and gold-based backside metallization to facilitate a conductive epoxy die attach process. All chips are screened for gain, output power and S-parameters prior to shipment for guaranteed performance. Designed for 27–31 GHz LMDS and digital radio bands.

Chip Outline



Dimensions indicated in mm.

All DC (V) pads are 0.1 x 0.1 mm and RF In, Out pads are 0.07 mm wide. Chip thickness = 0.1 mm.

Absolute Maximum Ratings

Characteristic	Value	
Operating Temperature (T _C)	-55°C to +90°C	
Storage Temperature (T _{ST})	-65°C to +150°C	
Bias Voltage (V _D)	7 V _{DC}	
Power In (P _{IN})	16 dBm	
Junction Temperature (T _J)	175°C	

Electrical Specifications at 25°C ($V_{DS} = 6 V$)

Parameter	Condition	Symbol	Min.	Typ. ²	Max.	Unit
Drain Current		I _{DS}		145	200	mA
Small Signal Gain	F = 27–31 GHz	G	17	19		dB
Input Return Loss	F = 27–31 GHz	RL		-10	-6	dB
Output Return Loss	F = 27–31 GHz	RL _O		-10	-6	dB
Output Power at 1 dB Gain Compression	F = 28 GHz	P _{1 dB}	14	16		dBm
Saturated Output Power	F = 28 GHz	P _{SAT}	15	18		dBm
Thermal Resistance ¹		Θ _{JC}		101		°C/W

1. Calculated value based on measurement of discrete FET.

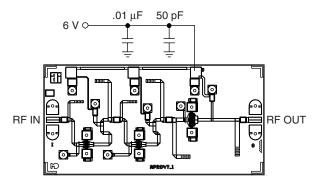
2. Typical represents the median parameter value across the specified

frequency range for the median chip.

Typical Performance Data

30 20 S₂₁ 10 0 S₁₁ (dB) -10 S₂₂ -20 -30 S₁₂ -40 -50 28 26 30 32 Frequency (GHz) **Typical Small Signal Performance** S-Parameters (V_{DS} = 6 V)

Bias Arrangement



For biasing on, adjust V_{DS} from zero to the desired value (6 V recommended). For biasing off, reverse the biasing on procedure.

Circuit Schematic

